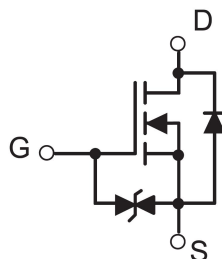
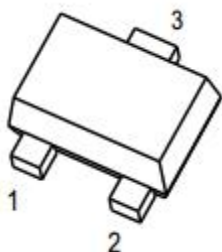


N Channel Advanced Power MOSFET

SOT-723



MARKING: KF

FEATURES

- Lead Free Product is Acquired
- Surface Mount Package
- N-Channel Switch with Low $R_{DS(on)}$
- Operated at Low Logic Level Gate Drive

APPLICATION

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
20 V	380mΩ@ 4.5V	0.75A
	450mΩ@ 2.5V	
	800mΩ@ 1.8V	

Maximum ratings ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

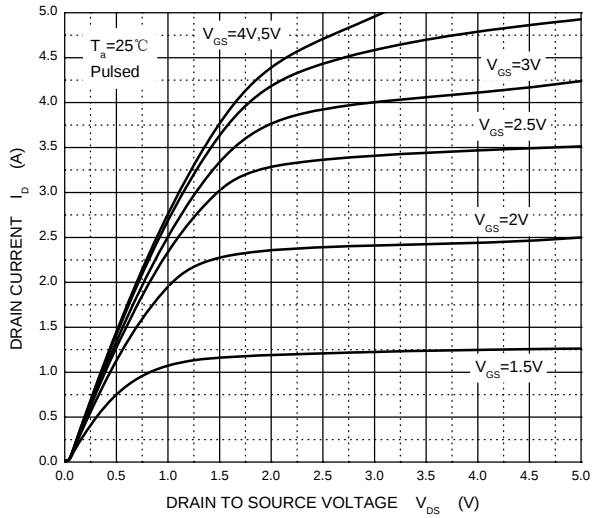
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Typical Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current (note 1)	I_D	0.75	A
Pulsed Drain Current ($t_p=10\mu s$)	I_{DM}	1.8	A
Power Dissipation (note 1)	P_D	150	mW
Thermal Resistance from Junction to Ambient (note 1)	$R_{\theta JA}$	833	$^{\circ}\text{C/W}$
Operation Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^{\circ}\text{C}$
Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	T_L	260	$^{\circ}\text{C}$

$T_a=25^{\circ}\text{C}$ unless otherwise specified

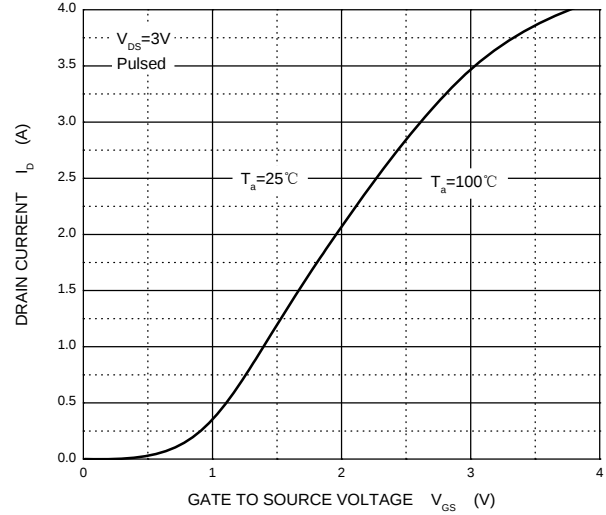
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =20V,V _{GS} = 0V			1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±10V, V _{DS} = 0V			±20	μA
Gate threshold voltage (note 2)	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.35	0.54	1.1	V
Drain-source on-resistance (note 2)	R _{DS(on)}	V _{GS} =4.5V, I _D =0.65A		270	380	mΩ
		V _{GS} =2.5V, I _D =0.55A		320	450	mΩ
		V _{GS} =1.8V, I _D =0.45A		390	800	mΩ
Forward transconductance (note 2)	g _{FS}	V _{DS} =10V, I _D =0.8A		1.6		S
Diode forward voltage	V _{SD}	I _S =0.15A, V _{GS} = 0V			1.2	V
DYNAMIC CHARACTERISTICS (note 4)						
Input capacitance	C _{iss}	V _{DS} =16V,V _{GS} =0V,f =1MHz		79	120	pF
Output capacitance	C _{oss}			13	20	pF
Reverse transfer capacitance	C _{rss}			9	15	pF
SWITCHING CHARACTERISTICS (note 4)						
Turn-on delay time (note 3)	t _{d(on)}	V _{GS} =4.5V,V _{DS} =10V, I _D =500mA,R _{GEN} =10Ω		6.7		ns
Turn-on rise time (note 3)	t _r			4.8		ns
Turn-off delay time (note3)	t _{d(off)}			17.3		ns
Turn-off fall time (note 3)	t _f			7.4		ns
Total Gate Charge (note 3)	Q _g	V _{DS} =10V,V _{GS} =4.5V,I _D =0.25A		750		pC
Gate-Source Charge (note 3)	Q _{gs}			75		pC
Gate-Drain Charge (note 3)	Q _{gd}			225		pC

Typical Characteristics

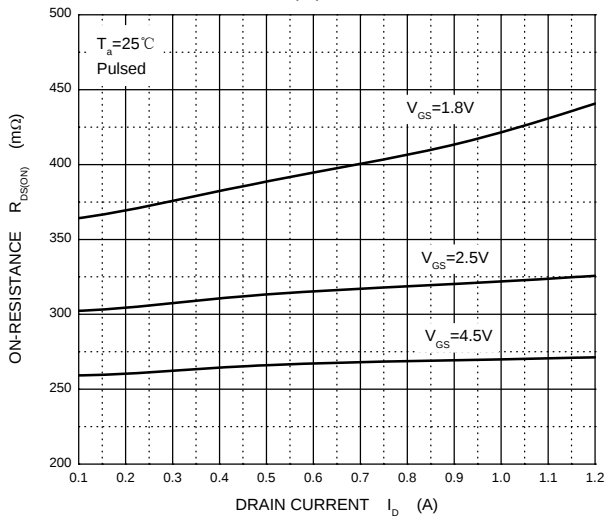
Output Characteristics



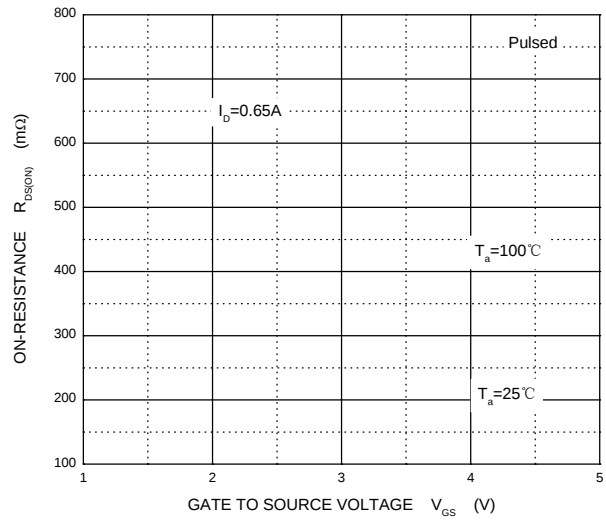
Transfer Characteristics



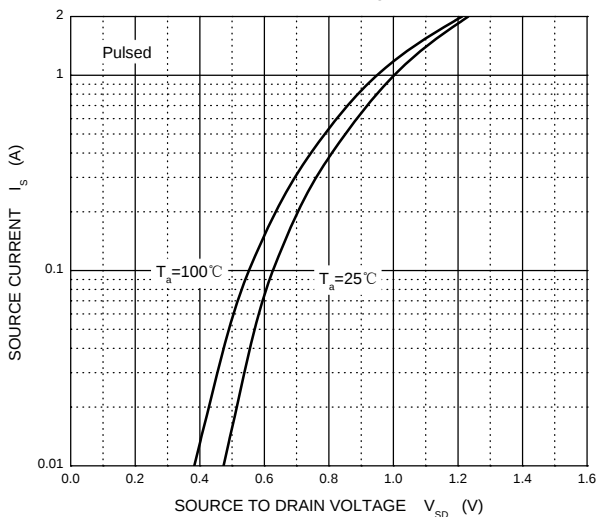
$R_{DS(ON)}$ — I_D



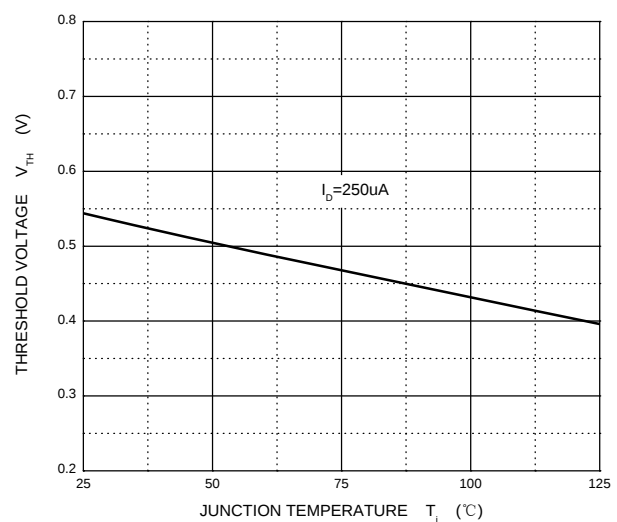
$R_{DS(ON)}$ — V_{GS}

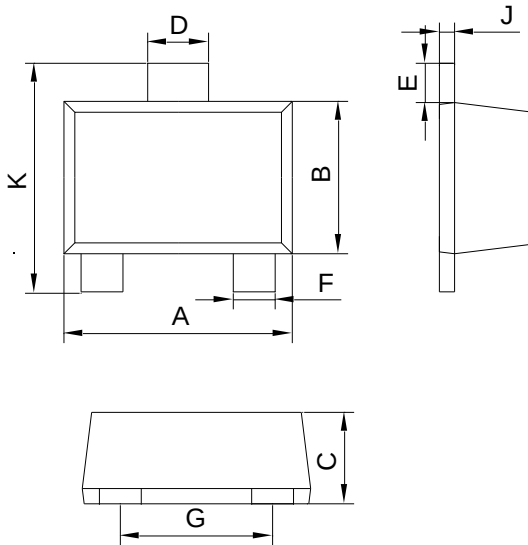


I_S — V_{SD}



Threshold Voltage





SOT-723		
Dim	Min	Max
A	1.10	1.30
B	0.70	0.90
C	0.40	0.54
D	0.22	0.42
E	0.10	0.30
F	0.12	0.32
G	0.70	0.90
J	0.08	0.15
K	1.10	1.30

